

2SK1104

Silicon N-Channel Junction FET

For switching

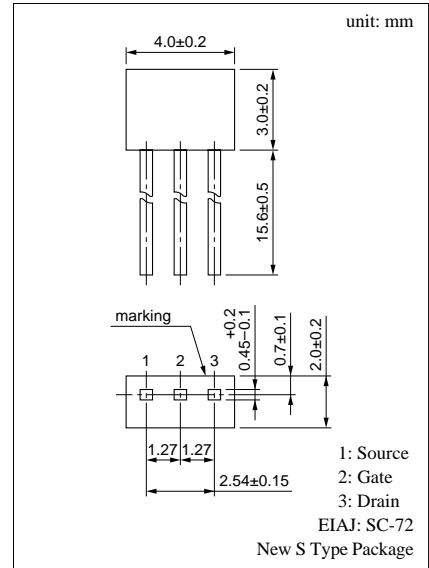
Complementary to 2SJ164

■ Features

- Low ON-resistance
- Low-noise characteristics

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rated	Unit
Gate to Drain voltage	V_{GDS}	-65	V
Drain current	I_D	20	mA
Gate current	I_G	10	mA
Allowable power dissipation	P_D	300	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C



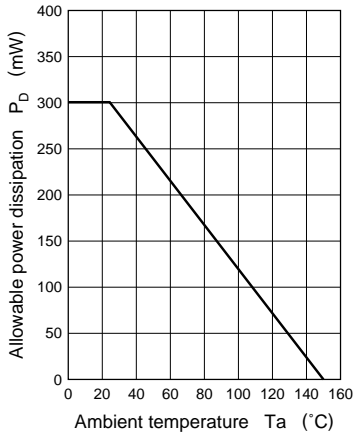
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}^*	$V_{DS} = 10V, V_{GS} = 0$	0.2		6	mA
Gate to Source leakage current	I_{GSS}	$V_{GS} = -30V, V_{DS} = 0$			-10	nA
Gate to Drain voltage	V_{GDS}	$I_G = -10\mu A, V_{DS} = 0$	-65			V
Gate to Source cut-off voltage	V_{GSC}	$V_{DS} = 10V, I_D = 10\mu A$		-1.5	-3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 1mA, f = 1kHz$	1.8	2.5		mS
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{DS} = 10mV, V_{GS} = 0$		250		Ω
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		7		pF
Output capacitance (Common Source)	C_{oss}			1.3		pF
Reverse transfer capacitance (Common Source)	C_{rss}			1.5		pF

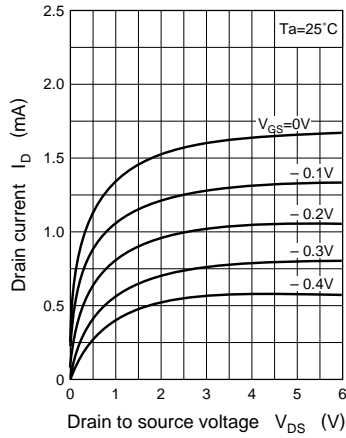
* I_{DSS} rank classification

Rank	O	P	Q	R
I_{DSS} (mA)	0.2 to 1	0.6 to 1.5	1 to 3	2.5 to 6

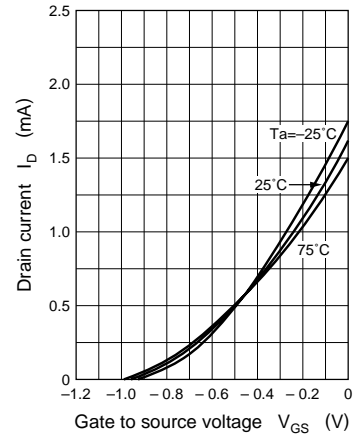
$P_D - T_a$



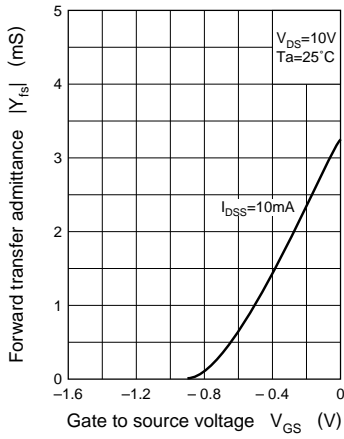
$I_D - V_{DS}$



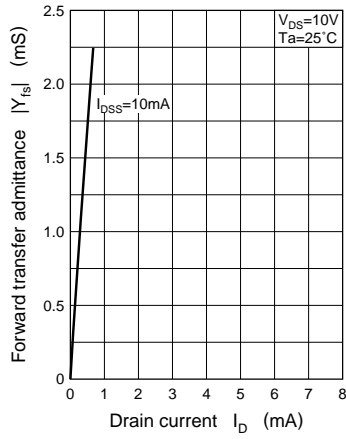
$I_D - V_{GS}$



$|Y_{fs}| - V_{GS}$



$|Y_{fs}| - I_D$



$C_{iss}, C_{oss}, C_{rss} - V_{DS}$

